

DHG10I1200PA

preliminary

 $V_{RRM} = 1200 V$

 $I_{FAV} = 10 A$

 t_{rr} = 200 ns

Sonic Fast Recovery Diode

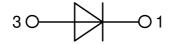
High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

Part number

DHG10I1200PA



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
 Vary about reasons times
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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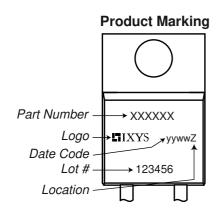
Fast Dio	de			1	Ratings	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ing voltage	$T_{VJ} = 25^{\circ}C$			1200	V
V_{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			1200	V
IR	reverse current, drain current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			15	μΑ
		$V_R = 1200 \text{ V}$	$T_{VJ} = 125^{\circ}C$			0.2	mΑ
V _F	forward voltage drop	I _F = 10 A	$T_{VJ} = 25^{\circ}C$			2.22	٧
		$I_F = 20 A$				2.93	٧
		I _F = 10 A	T _{VJ} = 125°C			2.23	V
		$I_F = 20 A$				3.14	٧
IFAV	average forward current	T _C = 105°C	T _{vJ} = 150°C			10	Α
		rectangular $d = 0.5$					1 1 1 1
V _{F0}	threshold voltage	and addition only	T _{VJ} = 150°C			1.25	٧
r _F	slope resistance	oss calculation only				90	mΩ
R _{thJC}	thermal resistance junction to case	e				1.5	K/W
R _{thCH}	thermal resistance case to heatsir	nk			0.5		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			85	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			60	Α
CJ	junction capacitance	$V_R = 600 \text{V} f = 1 \text{MHz}$	$T_{VJ} = 25^{\circ}C$		4		рF
I _{RM}	max. reverse recovery current	\	$T_{VJ} = 25 ^{\circ}\text{C}$		9		Α
		$I_F = 10 \text{ A}; V_R = 600 \text{ V}$	$T_{VJ} = 125 ^{\circ}\text{C}$		10.5		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 10 \text{ A}; V_R = 600 \text{ V} \\ -di_F /dt = 250 \text{ A}/\mu\text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}\text{C}$		200		ns
)	$T_{VJ} = 125$ °C		350		ns
				1		1	



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Package TO-220				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal			35	Α	
T _{VJ}	virtual junction temperature		-55		150	°C	
Top	operation temperature		-55		125	°C	
T _{stg}	storage temperature		-55		150	°C	
Weight				2		g	
M _D	mounting torque		0.4		0.6	Nm	
F _c	mounting force with clip		20		60	Ν	



Part description

D = Diode

H = Sonic Fast Recovery Diode

G = extreme fast

10 = Current Rating [A]

I = Single Diode

1200 = Reverse Voltage [V]

PA = TO-220AC (2)

Orderin	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standar	DHG10I1200PA	DHG10I1200PA	Tube	50	505273

Similar Part	Package	Voltage class	
DHG10I1200PM	TO-220ACFP (2)	1200	

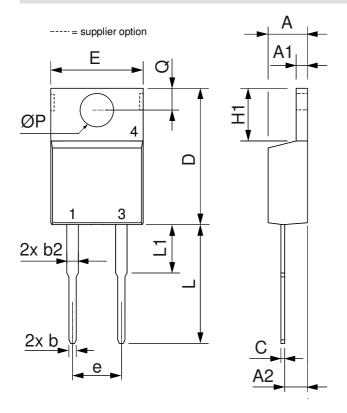
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150$ °C
$I \rightarrow V_0$)— <u>R</u> o	Fast Diode		
V _{0 max}	threshold voltage	1.25		V
$R_{0 \text{ max}}$	slope resistance *	87		$m\Omega$





preliminary

Outlines TO-220



Dim.	Millimeter		Incl	nes
	Min.	Max.	Min.	Max.
Α	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
С	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
е	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125





Fast Diode

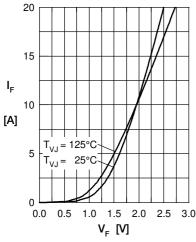


Fig. 1 Typ. Forward current versus V_F

Fig. 4 Dynamic parameters

 Q_{rr} , I_{RM} versus T_{VJ}

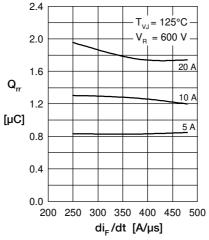


Fig. 2 Typ. reverse recov. charge Q_{rr} versus di/dt

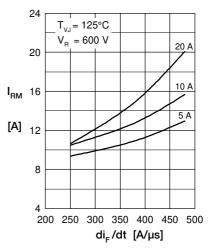


Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

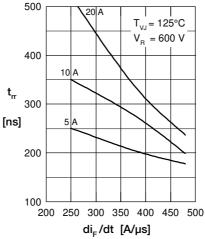


Fig. 5 Typ. recovery time t_{rr} versus di/dt

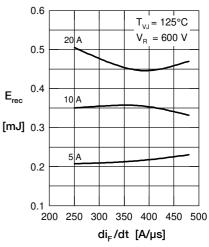


Fig. 6 Typ. recovery energy $E_{\rm rec}$ versus di/dt

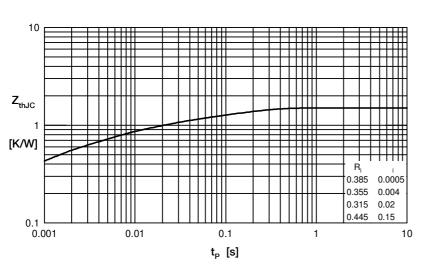


Fig. 7 Typ. transient thermal impedance junction to case

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